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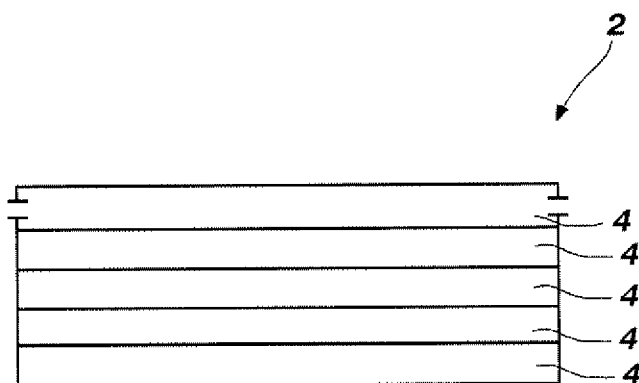
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(54) Title: METHOD OF FORMING A STRUCTURE HAVING A HIGH DIELECTRIC CONSTANT AND A STRUCTURE HAVING A HIGH DIELECTRIC CONSTANT



(57) Abstract: A method of forming a dielectric structure, such as a layer, is disclosed. The method comprises forming a high-k structure from a plurality of portions of a high-k material. Each of the plurality of portions of the high-k material is formed by depositing a plurality of monolayers of the high-k material and annealing the high-k material. The high-k material may be a perovskite-type material including, but not limited to, strontium titanate. A dielectric structure, a capacitor incorporating a dielectric structure and a method of forming a capacitor are also disclosed.